

Description

The SX80N06NF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 60V$ $I_D = 80A$

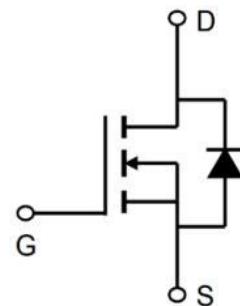
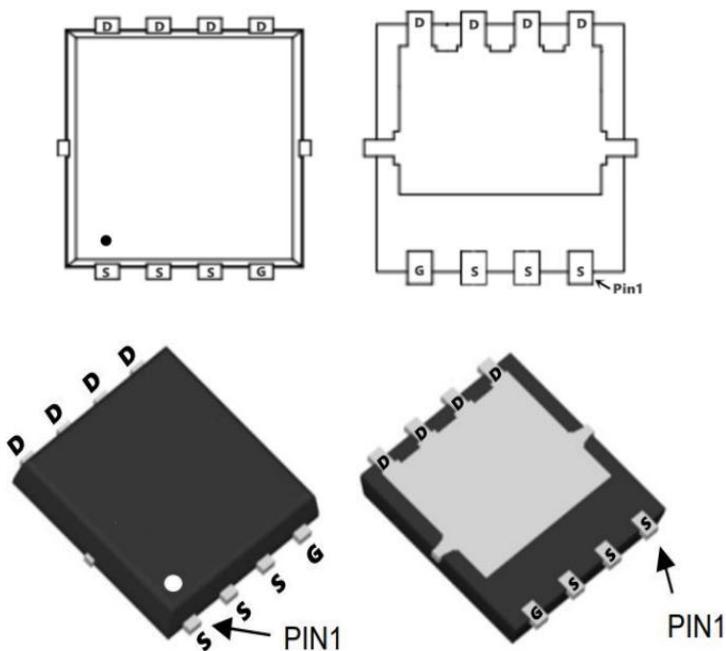
$R_{DS(ON)} < 6.0m\Omega$ @ $V_{GS}=10V$

Application

Battery protection

Load switch

Uninterruptible power supply

**Absolute Maximum Ratings@ $T_j=25^\circ C$ (unless otherwise specified)**

Symbol	Parameter	Value	Unit
V_{DS}	Drain source voltage	60	V
V_{GS}	Gate source voltage	± 20	V
$I_D @ T_c=25^\circ C$	Continuous drain current ¹⁾	80	A
$I_D @ T_c=100^\circ C$	Continuous drain current ¹⁾	45	A
IDM	Pulsed drain current ²⁾	210	A
I_{AS}	Diode forward current	70	A
$P_D @ T_c=25^\circ C$	Power dissipation	87	W
E_{AS}	Single pulsed avalanche energy ³⁾	66	mJ
T_{stg}, T_j	Operation and storage temperature	-55 to 150	°C
$R_{\theta JC}$	Thermal resistance, junction-case	1.44	°C/W
$R_{\theta JA}$	Thermal resistance, junction-ambient ⁴⁾	62	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Test condition	Min.	Typ.	Max	Unit
BVDSS	Drain-source breakdown voltage	$V_{GS}=0\text{ V}$, $I_D=250\text{ }\mu\text{A}$	60	72		V
VGS(th)	Gate threshold voltage	$V_{DS}=V_{GS}$, $I_D=250\text{ }\mu\text{A}$	1.2	1.8	2.5	V
RDS(ON)	Drain-source on-state resistance	$V_{GS}=10\text{ V}$, $I_D=20\text{ A}$		4.5	6.0	$\text{m}\Omega$
RDS(ON)	Drain-source on-state resistance	$V_{GS}=4.5\text{ V}$, $I_D=10\text{ A}$		6.4	10	$\text{m}\Omega$
IGSS	Gate-source leakage current	$V_{GS}=\pm 20\text{ V}$			± 100	nA
IDSS	Drain-source leakage current	$V_{DS}=60\text{ V}$, $V_{GS}=0\text{ V}$			1	μA
Rg	Gate Resistance	$f=1\text{MHz}$		2.8		Ω
Ciss	Input capacitance	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=100\text{ kHz}$		2136		pF
Coss	Output capacitance			331.5		pF
Crss	Reverse transfer capacitance			10.6		pF
td(on)	Turn-on delay time	$V_{GS}=10\text{ V}$, $V_{DS}=50\text{ V}$, $R_G=2\text{ }\Omega$, $I_b=25\text{ A}$		22.9		ns
t _r	Rise time			6.5		ns
td(off)	Turn-off delay time			45.7		ns
t _f	Fall time			20.4		ns
Q _g	Total gate charge	$I_b=25\text{ A}$, $V_{DS}=50\text{ V}$, $V_{GS}=10\text{ V}$		30		nC
Q _{gs}	Gate-source charge			5.8		nC
Q _{gd}	Gate-drain charge			6.1		nC
V _{plateau}	Gate plateau voltage			3.6		V
VSD	Diode forward voltage	$I_s=20\text{ A}$, $V_{GS}=0\text{ V}$			1.3	V
trr	Reverse recovery time	$I_s=25\text{ A}$, $dI/dt=100\text{ A}/\mu\text{s}$		50.3		ns
Q _{rr}	Reverse recovery charge			45.1		nC
Irrm	Peak reverse recovery current			1.5		A

Note :

- 1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width .The EAS data shows Max. rating .
- 3、The power dissipation is limited by 175°C junction temperature
- 4、EAS condition: $T_J=25^\circ\text{C}$, $V_{DD}=25\text{V}$, $V_{GS}=10\text{V}$, $L=0.1\text{Mh}$, $I_{AS}=40\text{A}$
- 5、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Typical Characteristics

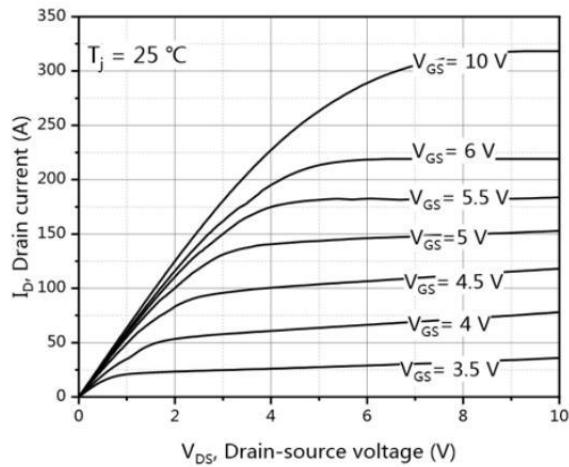


Figure 1. Type Output Characteristics

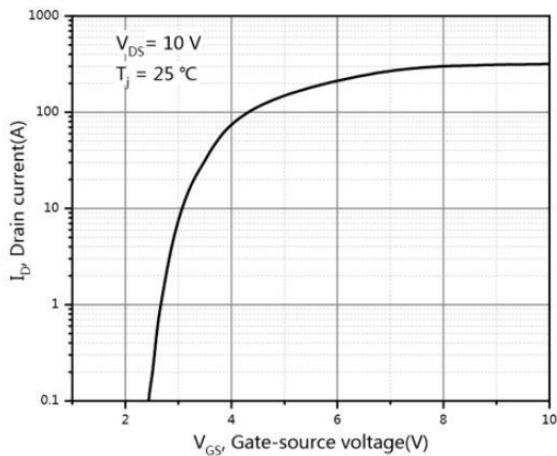


Figure 2. Type Transfer Characteristics

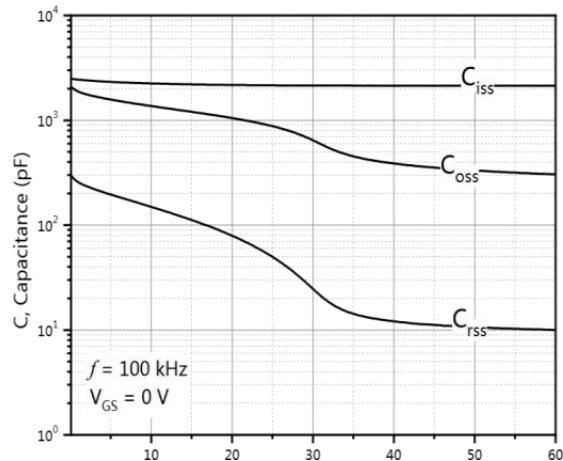


Figure 3. Type Capacitances

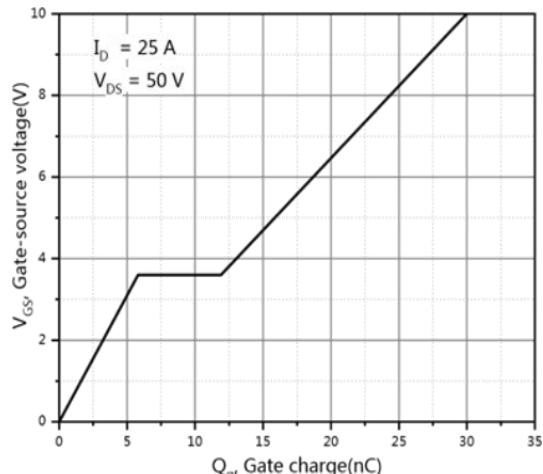


Figure 4. Type Gate Charge

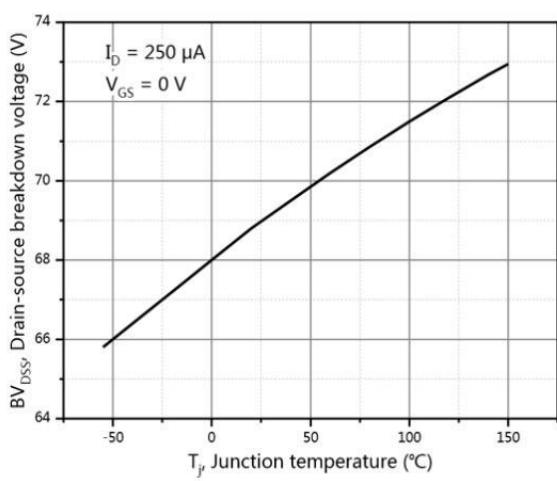


Figure 5. Drain-source Breakdown Voltage

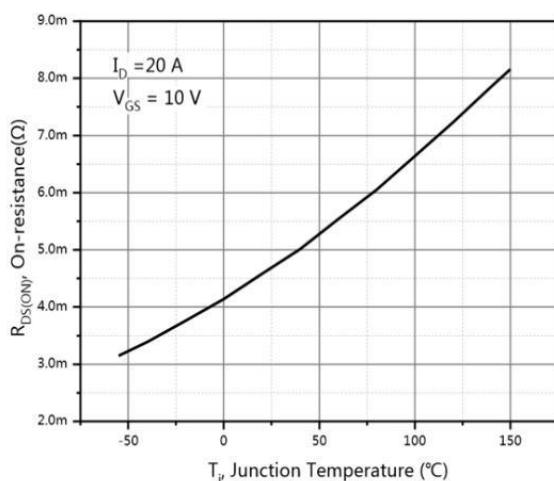


Figure 6. Drain-source on-state resistance

Typical Characteristics

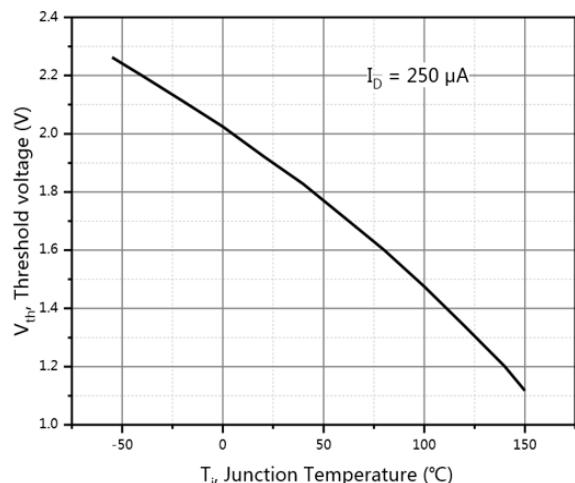


Figure 7.Threshold Voltage

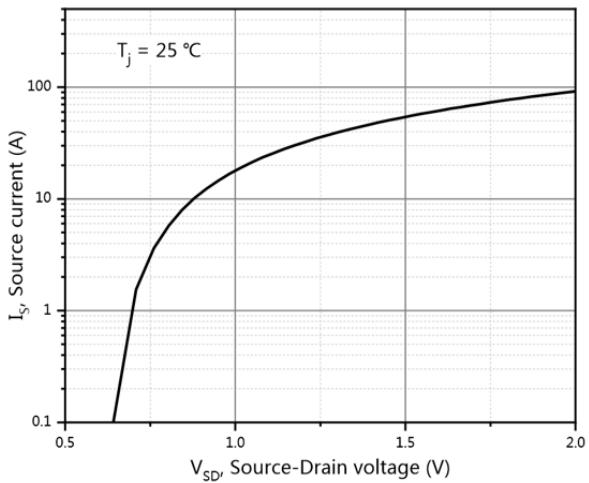


Figure 8.Forward characteristic of body diode

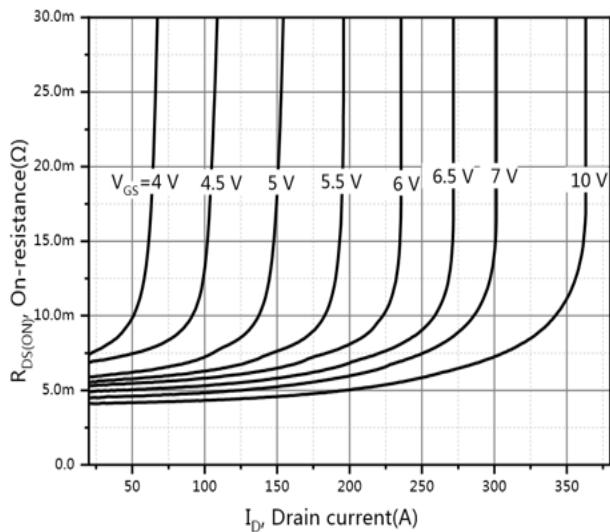


Figure 9.Drain-source on-state resistance

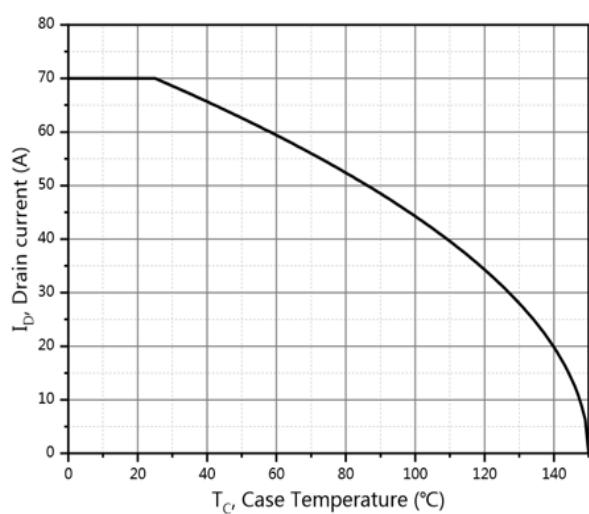


Figure 10.Drain-current

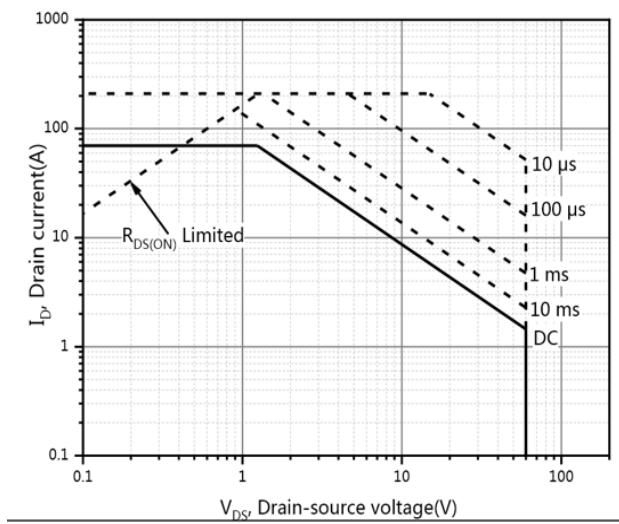


Figure 11.Safe operation area fo Tc=25°C

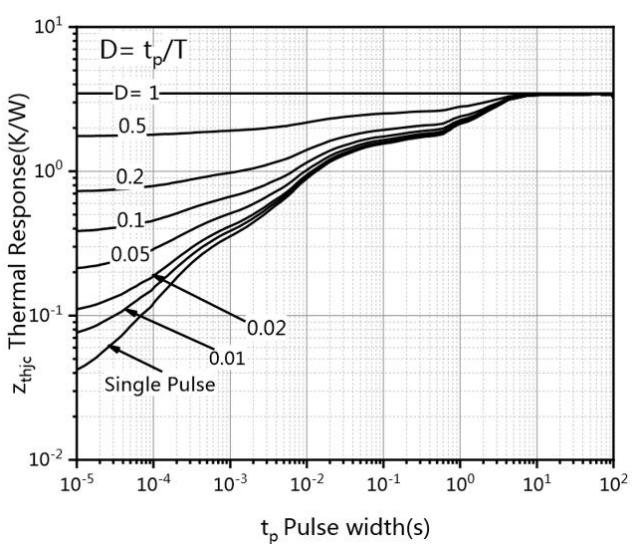
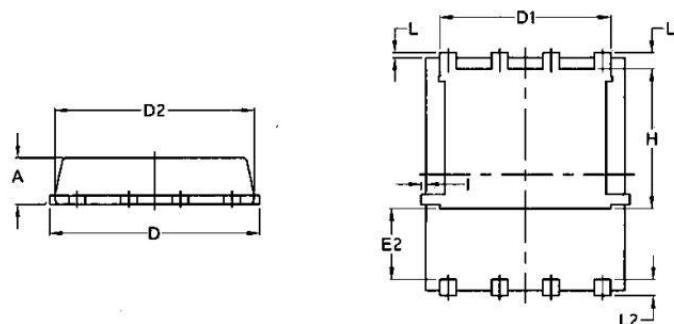
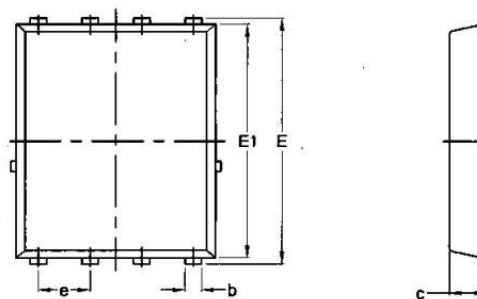


Figure 12.Safe operation area fo PDFN5*6-8L

Package Mechanical Data-PDFN5*6-8L-JQ Single



Symbol	Common			
	mm		Inch	
	Min	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	PDN5*6-8L		5000